



SemiNex delivers the highest available power at infrared wavelengths between 12xx and 19xx nm. When necessary we will further optimize the design of our InP laser chips to meet our customers' specific optical and electrical performance needs. Diodes, bars and packages are tested to meet customer and market performance demands. Typical results and packaging options are shown. Contact SemiNex for additional details or to discuss your specific requirements.Fast axis collimated to 5mrad with f=590um



TO-9 Packaged Laser Diode

High Power Single-Mode and Multi-Mode SemiNex

12xx to 19xx nm

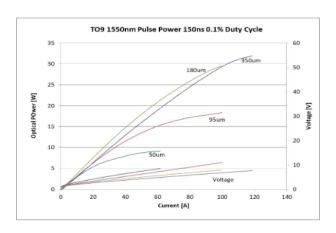
Custom Wavelengths Available Lensed Options Available

- Applications
 OEM Medical
 Professional Medical
- LiDAR
 Military / Aerospace
 Illumination

Features

- Cost effective
 High Output Power

- High Dynamic Range
 High Efficiency
 Standard Low Cost Package
 Fast axis collimated to 5mrad with f=590um lens









	Symbol	TO9-149-115	Units
Optical			
Wavelength	λ _c	1550	nm (±20)
Output Power (<10ns)	P ₀	70.00	watts (±10%)
Output Power (150ns)	P ₀	30.00	watts (±10%)
Chip Cavity Length	CL	2500	μm
No. of Junctions		1	
Emitter Width	W	350	μm
Emitter Height	Н	1	μm
Spectral Width	δλ	15	nm 3dB
Slope Efficiency	η۰	0.35	W/A
Fast Axis Div.*	⊝_perp	0.3	deg FWHM
Slow Axis Div.	O_parallel	10	deg FWHM
Electrical			
Power Conversion Eff.	η	3	%
Operating Current (<10ns)	I _{op}	100	A
Operating Current (150ns)	I _{op}	100	A
Threshold Current	I _{th}	3.8	A
Operating Voltage	V _{op}	6.6	V
Mechanical			
Weight	·	2	g
Operating Temp.**		-40 to 60	°C
Storage Temp.		-40 to 80	°C

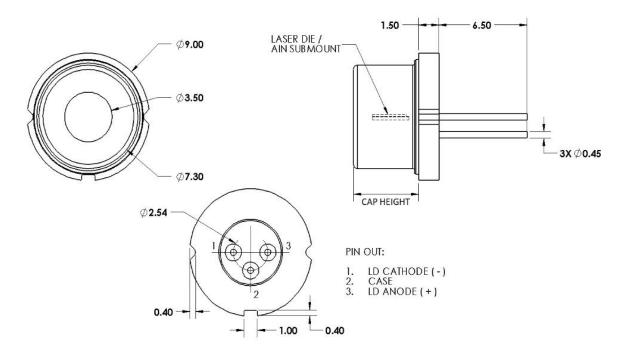
Specified values are rated at a constant heat sink temperature of 20°C.

**Specified operating conditions are based on 20°C heat sink temperature. High temperature operation will reduce performance and MTTF.

Unless otherwise indicated all values are nominal.

Uncapped TO9 specifications assume heatsinking underneath laser chip.

Capped TO9 specifications assume heatsinking only on flat surface where pins extend.



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